



# ACTT6G-800E

## AC Thyristor Triac power switch

Rev. 1 — 1 November 2011

Product data sheet

## 1. Product profile

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### 1.1 General description

AC Thyristor Triac power switch in a SOT226A (I2PAK) plastic package with self-protective clamping capabilities against low and high energy transients.

### 1.2 Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Sensitive gate for easy logic level triggering
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$

### 1.3 Applications

- AC Fan controllers
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Loads such as contactors, circuit breakers, valves, dispensers and door locks
- Pump motor circuits
- Reversing induction motor control



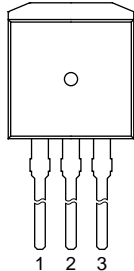
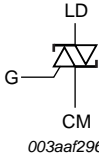
**1.4 Quick reference data**

**Table 1. Quick reference data**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; see <a href="#">Figure 5</a> ; see <a href="#">Figure 6</a>	-	-	51	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 108 °C; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 4</a>	-	-	6	A
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
V <sub>PP</sub>	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; see <a href="#">Figure 3</a>	-	-	2	kV

**2. Pinning information**

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common		
2	LD	load		
3	G	gate		
mb	LD	mounting base; load		

**SOT226A (I2PAK)**

**3. Ordering information**

**Table 3. Ordering information**

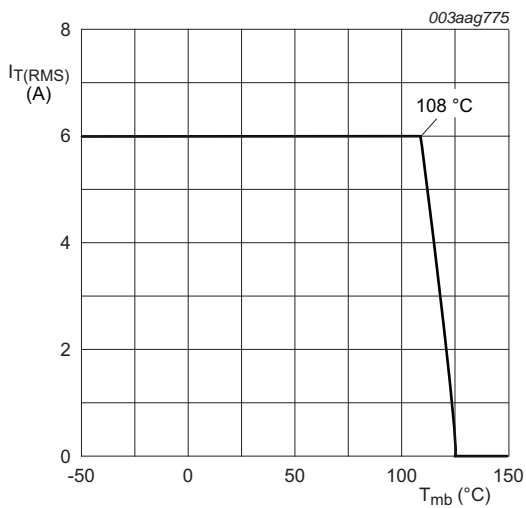
Type number	Package		Version
	Name	Description	
ACTT6G-800E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226A

### 4. Limiting values

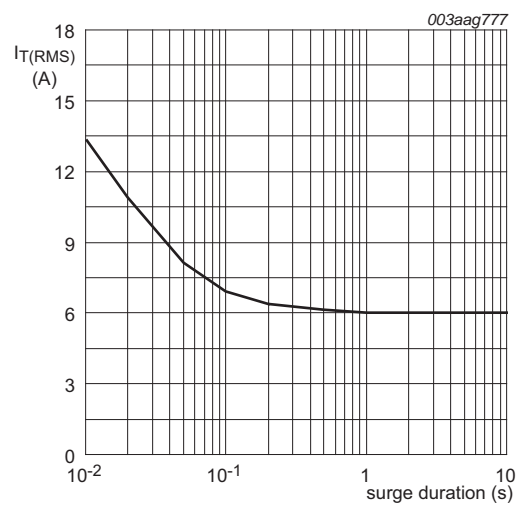
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 108\text{ °C}$ ; see <a href="#">Figure 1</a> ; see <a href="#">Figure 2</a> ; see <a href="#">Figure 4</a>	-	6	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(initial)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	56	A
		full sine wave; $T_{j(initial)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; see <a href="#">Figure 5</a> ; see <a href="#">Figure 6</a>	-	51	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	13	A <sup>2</sup> s
$dl_T/dt$	rate of rise of on-state current	$I_T = 9\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $dl_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/ $\mu\text{s}$
$I_{GM}$	peak gate current	$t = 20\text{ }\mu\text{s}$	-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ °C}$ ; non-repetitive, off-state; see <a href="#">Figure 3</a>	-	2	kV



**Fig 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 108\text{ °C}$

**Fig 2. RMS on-state current as a function of surge duration; maximum values**

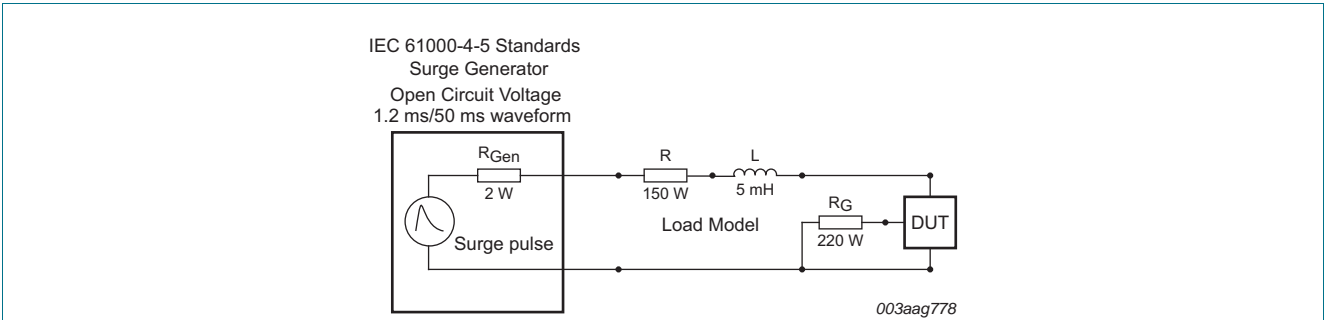


Fig 3. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

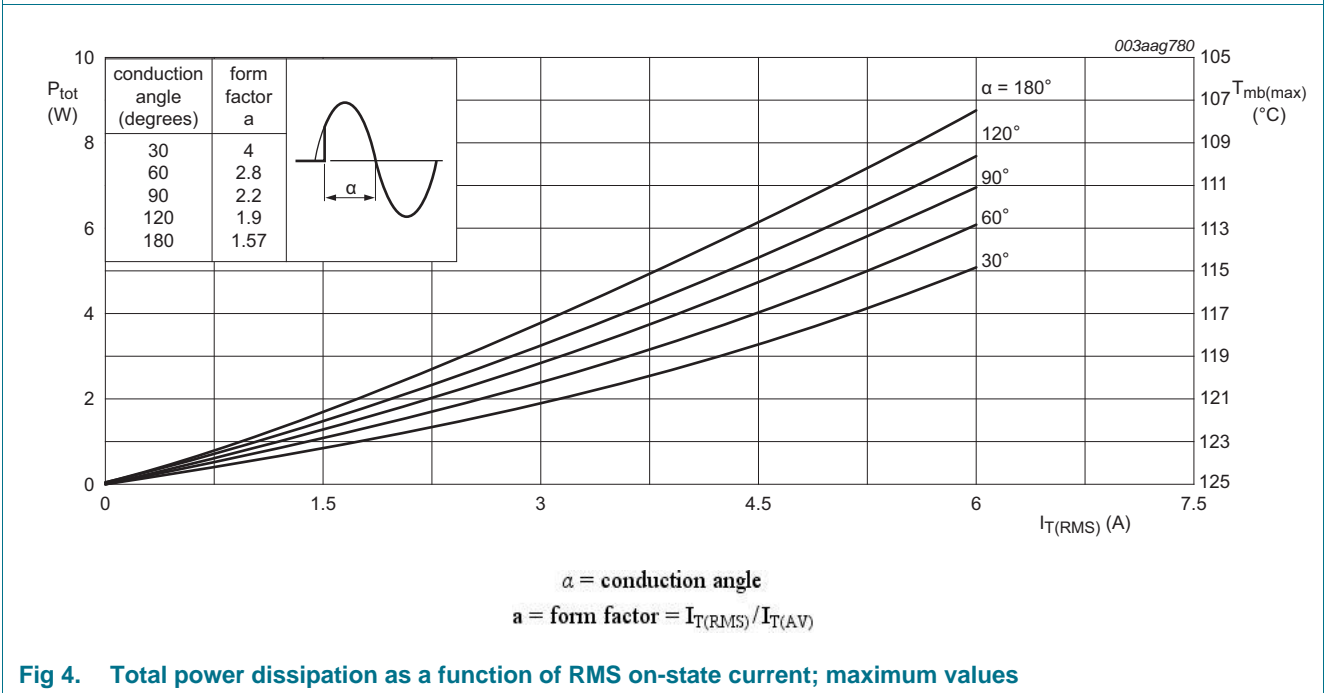
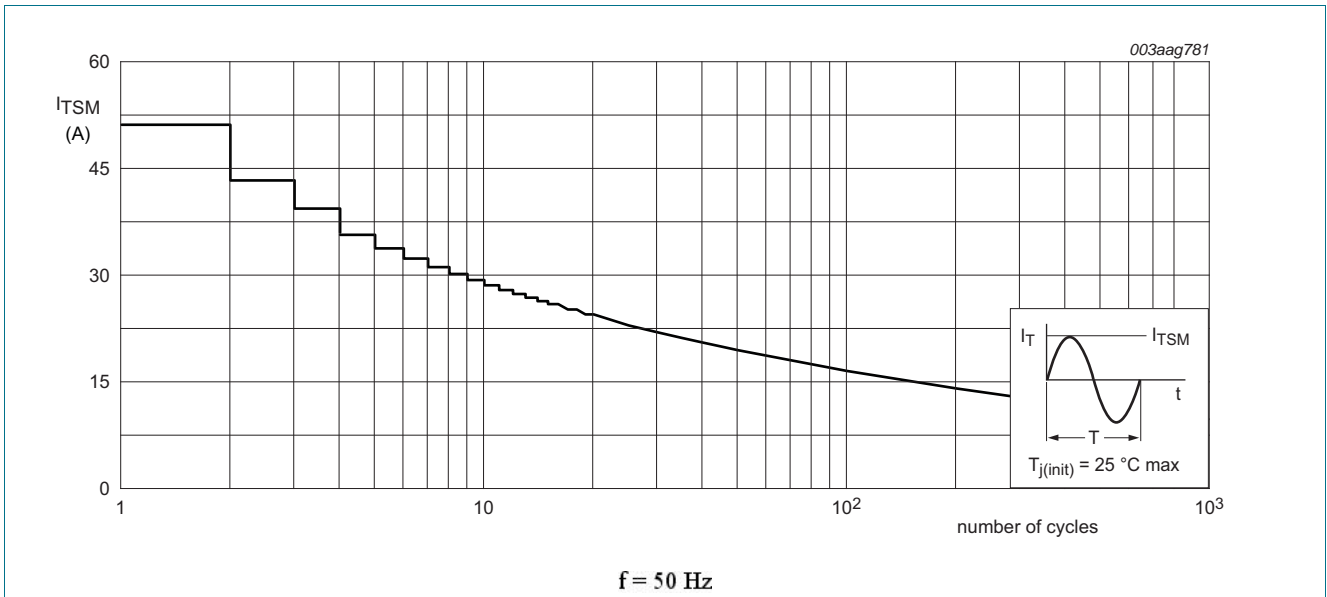
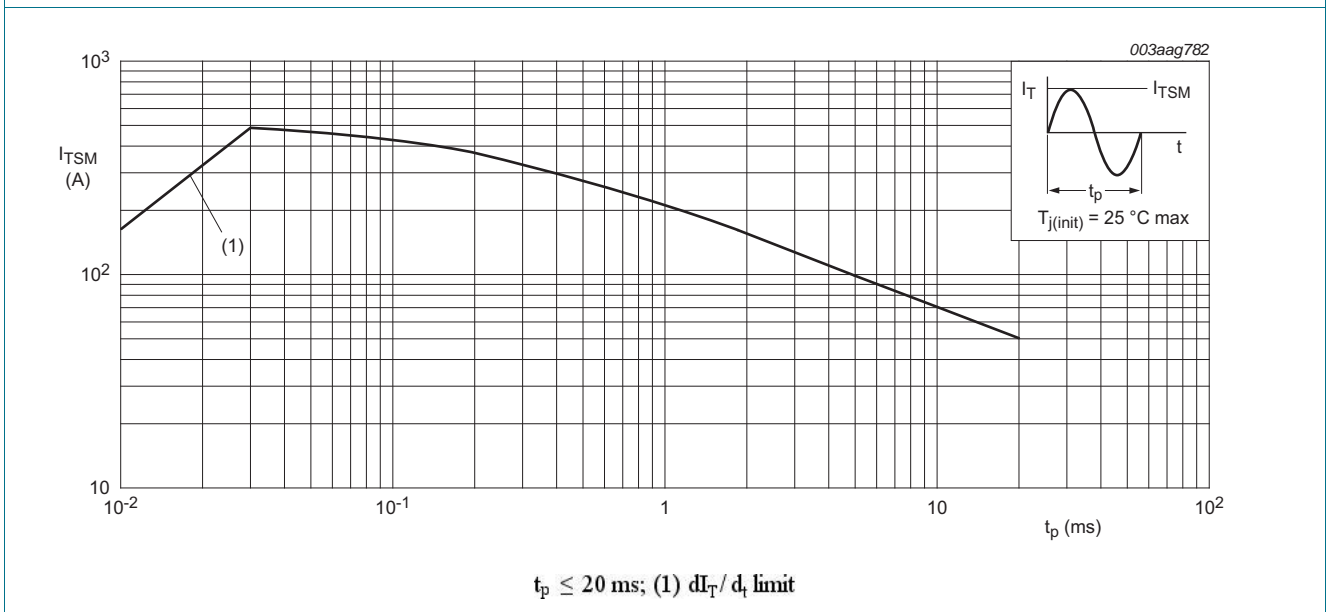


Fig 4. Total power dissipation as a function of RMS on-state current; maximum values



**Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**

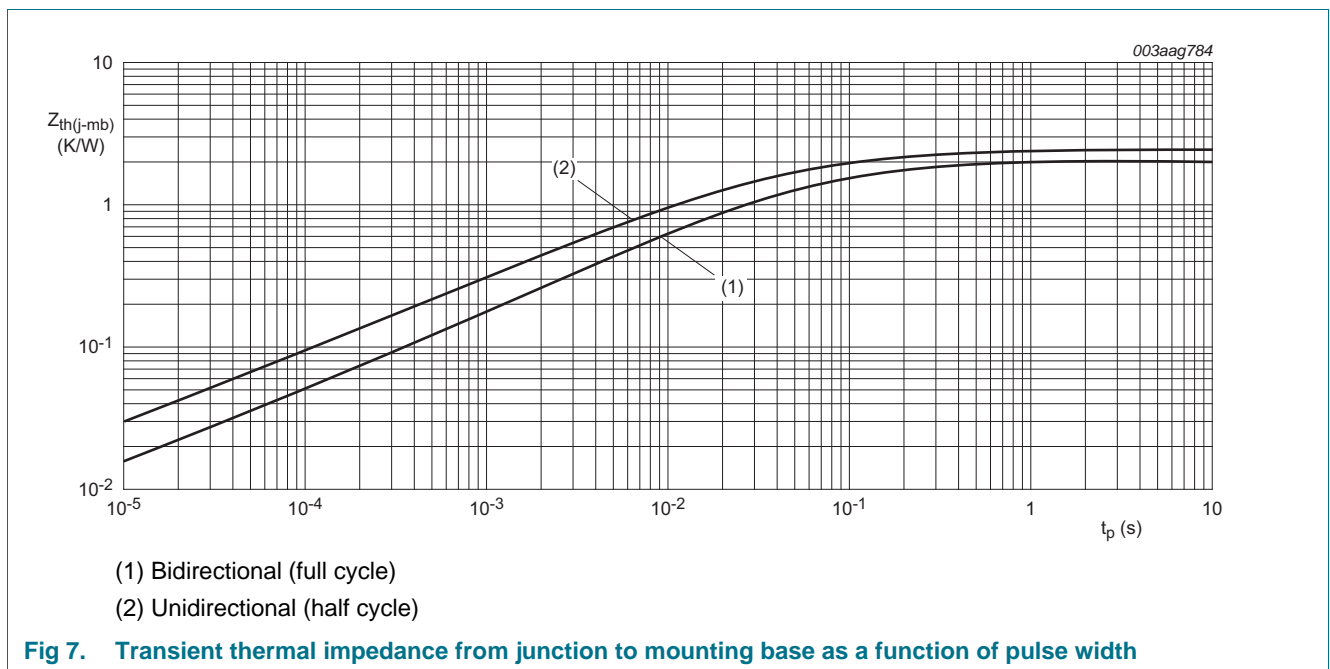


**Fig 6. Non-repetitive peak on-state current as a function of pulse width; maximum values**

## 5. Thermal characteristics

**Table 5. Thermal characteristics**

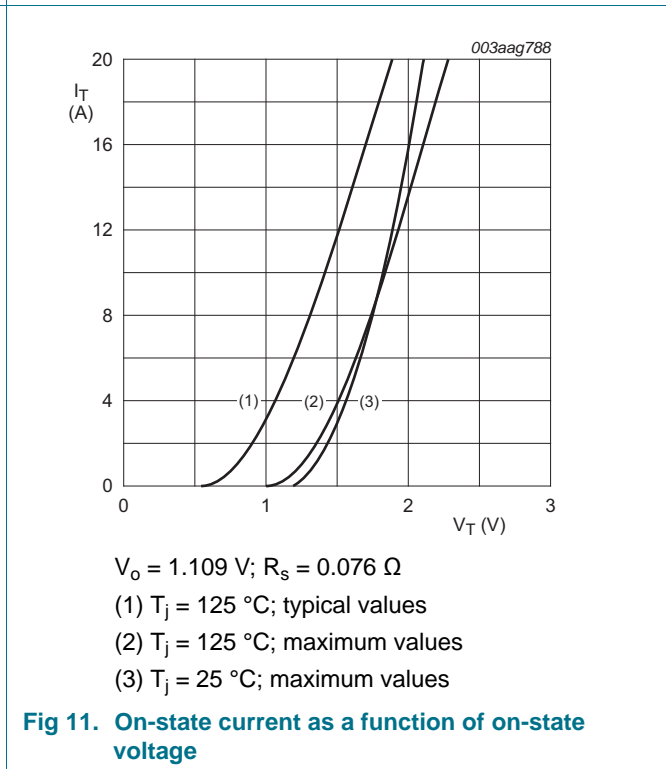
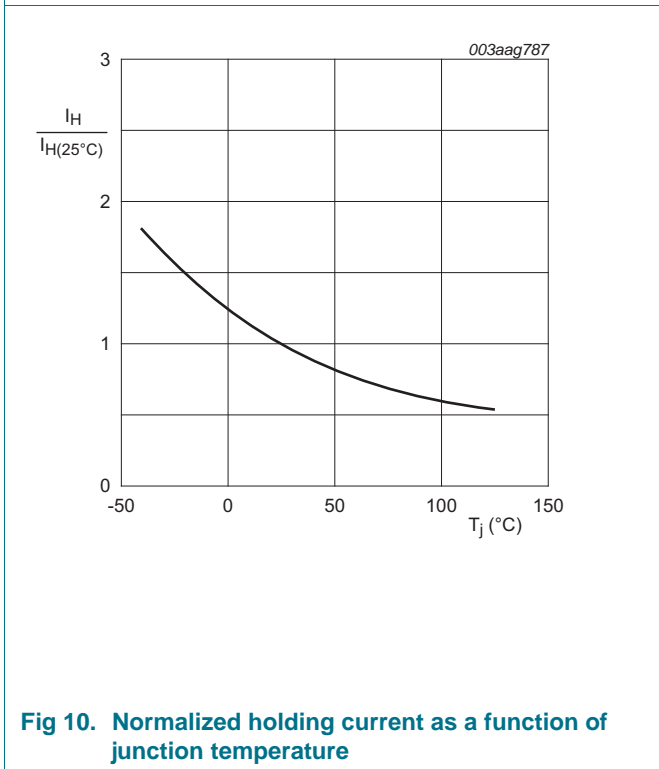
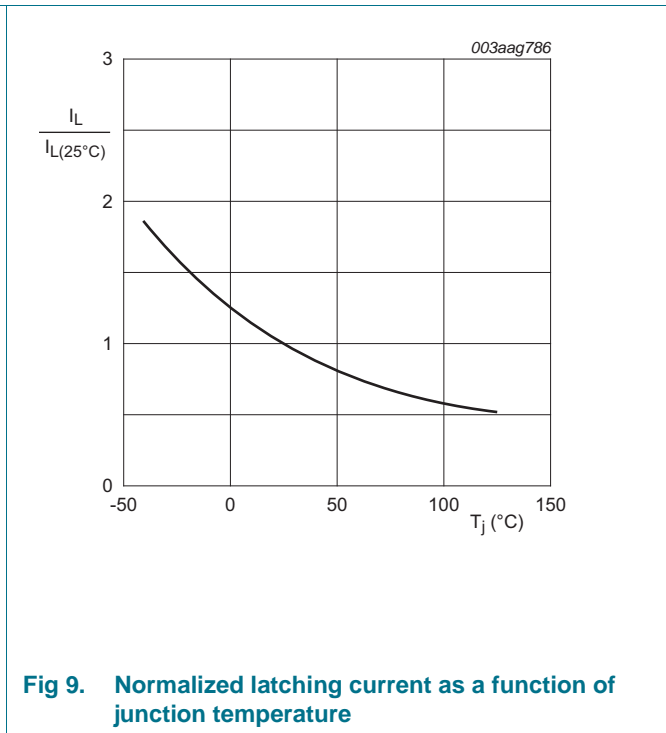
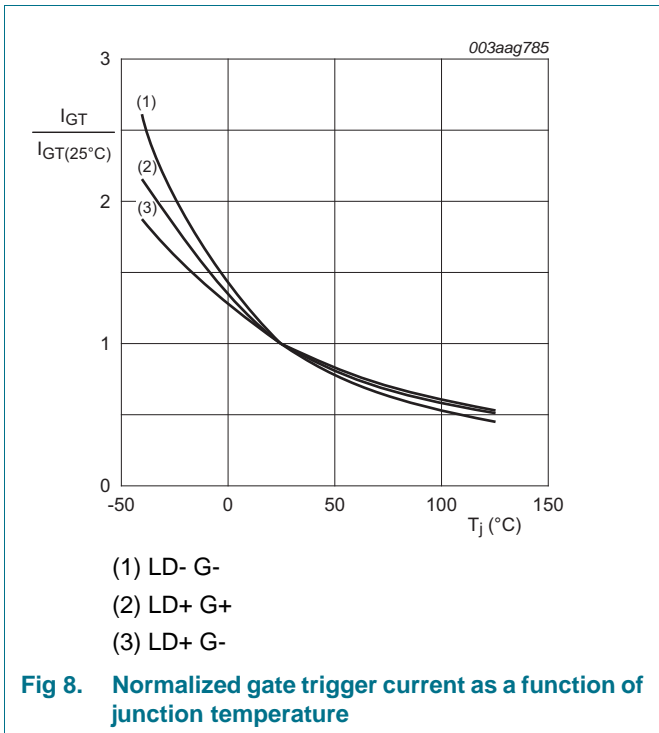
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	half cycle; see <a href="#">Figure 7</a>	-	-	2.4	K/W
		full cycle; see <a href="#">Figure 7</a>	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



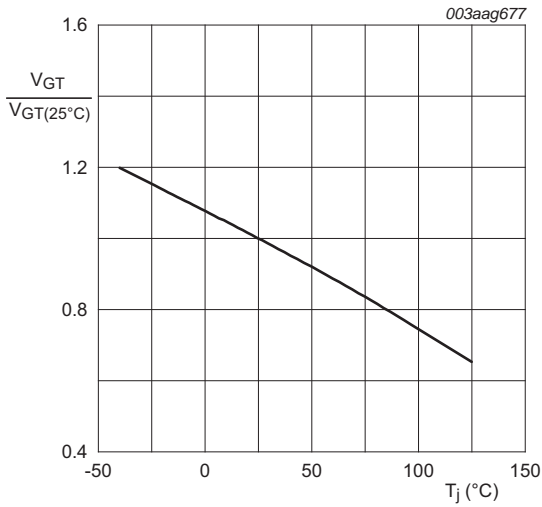
## 6. Characteristics

**Table 6. Characteristics**

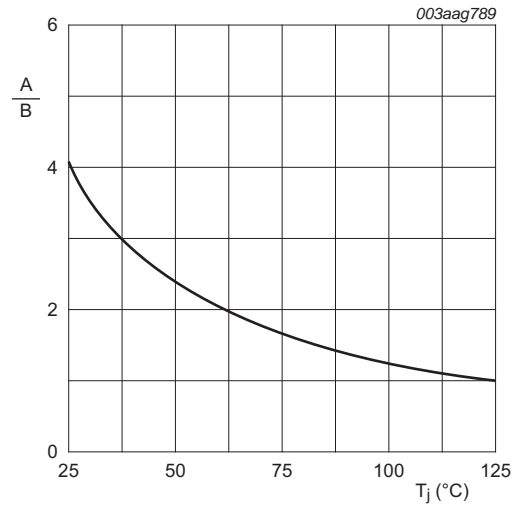
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	-	10	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 8</a>	-	-	10	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a>	-	-	30	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a>	-	-	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 9</a>	-	-	30	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 10</a>	-	-	25	mA
$V_T$	on-state voltage	$I_T = 8\text{ A}$ ; see <a href="#">Figure 11</a>	-	-	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 400\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 125\text{ °C}$ ; see <a href="#">Figure 12</a>	0.2	-	-	V
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	-	1.5	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}$ ; $T_j = 125\text{ °C}$	-	-	0.5	mA
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ °C}$ ; gate open circuit; exponential waveform; see <a href="#">Figure 13</a>	500	-	-	V/ $\mu\text{s}$
$di_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	3.5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	5	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	10	-	-	A/ms
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ °C}$	850	-	-	V





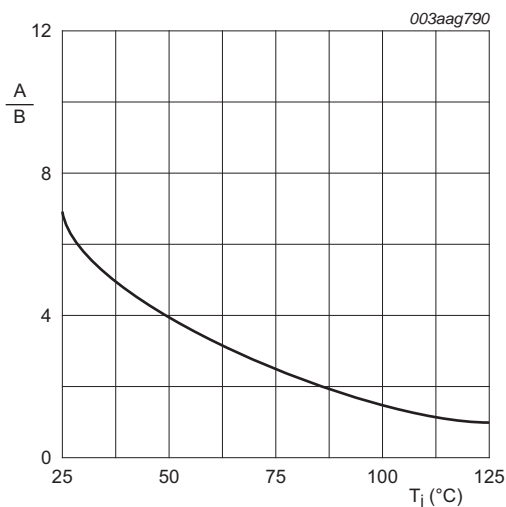


**Fig 12. Normalized gate trigger voltage as a function of junction temperature**



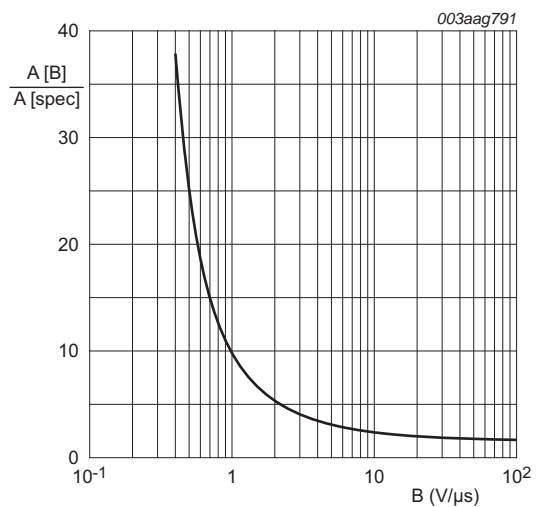
A is  $dV_D/dt$  at condition  $T_j$  °C  
 B is  $dV_D/dt$  at condition  $T_j$  125 °C

**Fig 13. Normalized rate of rise of off-state voltage as a function of junction temperature**



A is  $di_{com}/dt$  at condition  $T_j$  °C  
 B is  $di_{com}/dt$  at condition  $T_j$  125 °C  
 $V_D = 400$  V

**Fig 14. Normalized critical rate of rise of commutating current as a function of junction temperature**



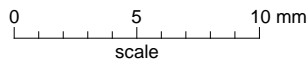
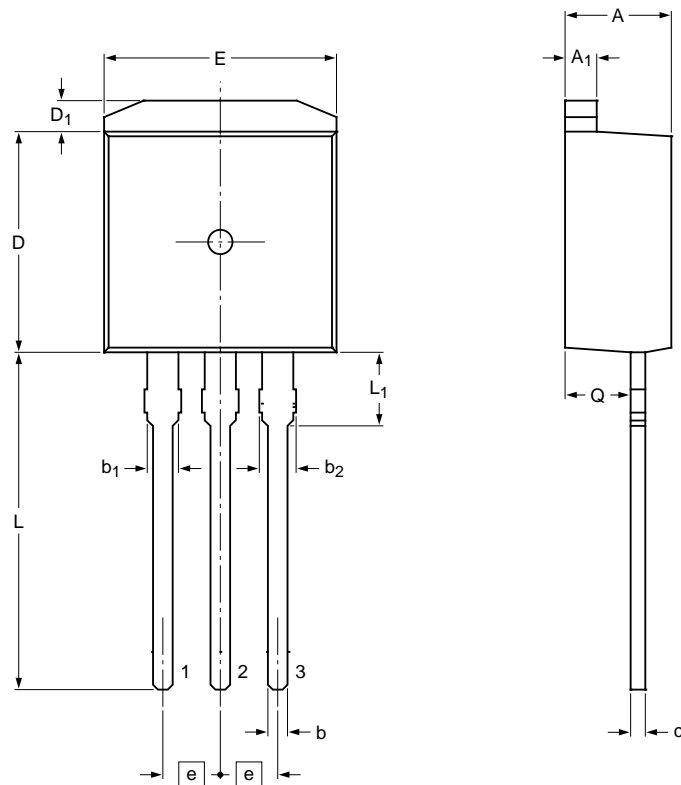
A[B] is  $di_{com}/dt$  at condition B,  $dV_{com}/dt$   
 A[spec] is the specified data sheet value of  $di_{com}/dt$   
 turn-off time < 20 ms

**Fig 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values**

**7. Package outline**

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226A



Dimensions

Unit	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub>	Q
max	4.7	1.40	0.95	1.40	1.7	0.65	9.4	1.32	10.30	2.54	15.0	3.0	2.6
nom										(REF)		(REF)	
min	4.3	1.15	0.70	1.14	1.3	0.45	8.6	1.02	9.65		12.5		2.2

sot226a\_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT226A		TO-262			09-08-17 09-08-25

**Fig 16. Package outline SOT226A (I2PAK)**

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ACTT6G-800E v.1	20111101	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1]</sup> <sup>[2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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